

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

1N4933GPP SERIES

GLASS PASSIVATED JUNCTION
FAST RECOVERY RECTIFIER
1.0 AMP, 50 THRU 600 VOLTS

JEDEC DO-41 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N4933GPP Series types are 1.0 Amp Glass Passivated Junction Fast Recovery Silicon Rectifiers which are high quality, well constructed, highly reliable components designed for high speed switching applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**
Note: Higher voltage devices are available in the CR1F-010GPP series.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

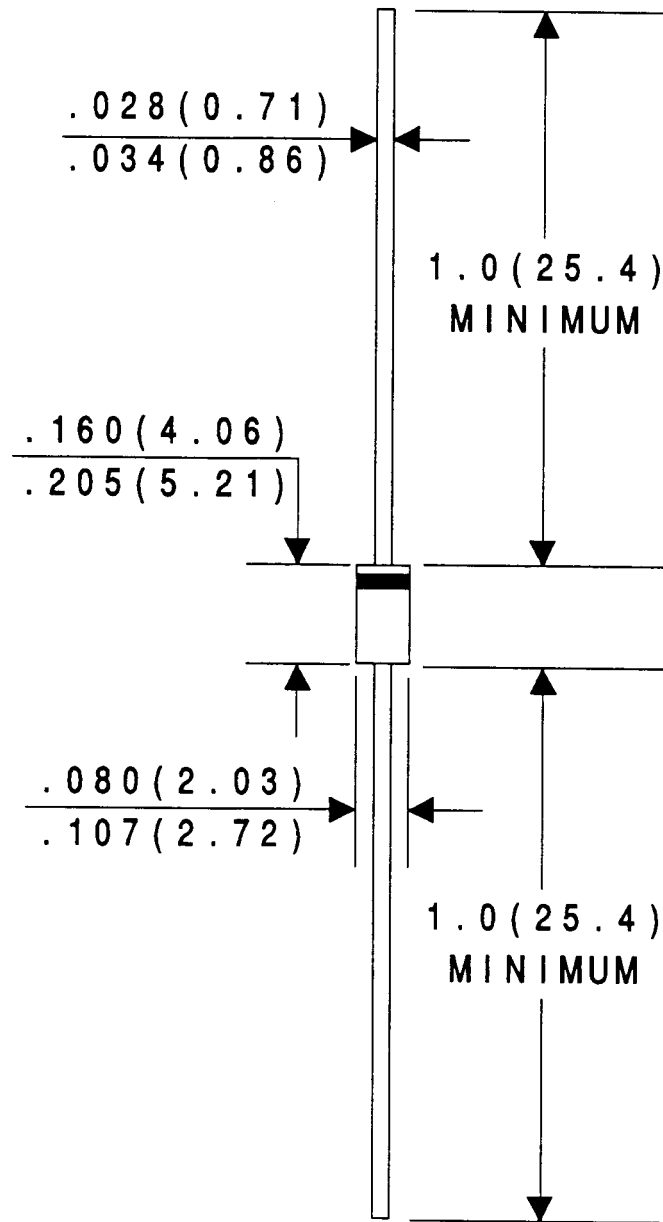
	SYMBOL	1N4933 GPP	1N4934 GPP	1N4935 GPP	1N4936 GPP	1N4937 GPP	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	50	100	200	400	600	V
DC Blocking Voltage	V_R	50	100	200	400	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	V
Average Forward Current ($T_A=75^{\circ}\text{C}$)	I_O			1.0			A
Peak Forward Surge Current ($T_A=75^{\circ}\text{C}$)	I_{FSM}			30			A
Operating and Storage							
Junction Temperature	T_J, T_{stg}			-65 to +175			$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}			50			$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_F	$I_F=1.0\text{A}$			1.3	V
I_R	$V_R=\text{Rated } V_{RRM}$			5.0	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=125^{\circ}\text{C}$			100	μA
t_{rr}	$I_F=1.0\text{A}, V_R=30\text{V}$			200	ns
C_J	$V_R=4.0\text{V}, f=1.0\text{MHz}$		15		pF

(SEE REVERSE FOR MECHANICAL OUTLINE)

JEDEC DO-41 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).